# 2SJ55,2SJ56

## HITACHI/(OPTOELECTRONICS)

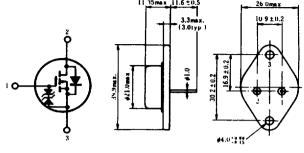
## SILICON P-CHANNEL MOS FET

## LOW FREQUENCY POWER AMPLIFIER

Complementary Pair with 2SK175, 2SK176

## **■** FEATURES

- High Power Gain.
- Excellent Frequency Response.
- High Speed Switching.
- Wide Area of Safe Operation.
- Enhancement-Mode.
- Good Complementary Characteristics.
- Equipped with Gate Protection Diodes.



(JEDEC TO-3)

1. Gate 2. Drain 3. Source (Case)

(Dimensions in mm)

## ■ ABSOLUTE MAXIMUM RATINGS ( $T_a=25$ °C)

T4	Symbol	Rating		Unit
Item		2SJ55	2SJ56	Unit
Drain-Source Voltage	V <sub>DSX</sub>	-180	-200	V
Gate-Source Voltage	$V_{GSS}$	±20		v
Drain Current	I <sub>D</sub>	-8		A
Body-Drain Diode Reverse Drain Current	IDR	-8		A
Channel Dissipation	Pch*	125		w
Channel Temperature	T <sub>ch</sub>	150		°C
Storage Temperature	Ting	-55 ~ +150		°C

<sup>\*</sup>Value at T, =25 °C

# POWER VS. TEMPERATURE DERATING

Case Temperature Tc (°C)

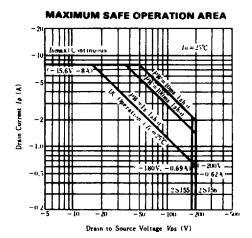
## ■ ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25 °C)

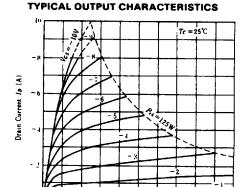
Item		Symbol	Test Condition	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	2SJ55	Viennsx	I <sub>D</sub> =-10mA, V <sub>GS</sub> =10V	-180	_		V
	2SJ56			-200	-	_	v
Gate-Source Breakdown Voltage		V <sub>(BR)GSS</sub>	$I_0 = \pm 100 \mu A$ , $V_{DS} = 0$	±20	_		v
Gate-Source Cutoff Voltage		V <sub>GStoff)</sub>	$I_D = -100 \text{mA}, V_{DS} = -10 \text{V}$	-0.15	_	-1.45	v
Drain-Source Saturation Voltage		V <sub>DS(sat)</sub>	$I_D = -8A, V_{GD} = 0^*$	_	_	-12	v
Forward Transfer Admittance	k/k	$I_{o}=-3A$ , $V_{os}=-10V^{*}$	0.7	1.0	1.4	s	
Input Capacitance		Cus	$V_{os} = 5V, V_{os} = -10V, f = 1MHz$		1000	_	рF
Output Capacitance		Coss			470	_	pF
Reverse Transfer Capacitance		Crss	1	_	50	_	рF
Turn-on Time		ton		_	320	_	ns
Turn-off Time		Larr	$V_{DD}$ =-30V, $I_D$ =-4A		120	_	ns

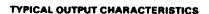
<sup>\*</sup>Pulse Test

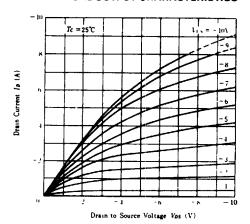
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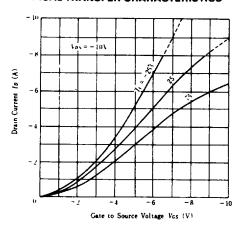




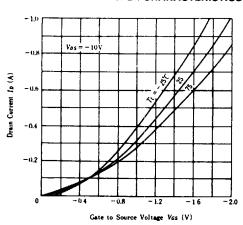




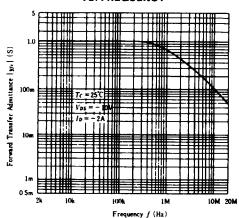
Drain to Source Voltage Vps (V)



### TYPICAL TRANSFER CHARACTERISTICS



# FORWARD TRANSFER ADMITTANCE VS. FREQUENCY



## HITACHI/(OPTOELECTRONICS)

